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APPLICATION NO.	FI	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/688,797 10/17/2003		0/17/2003	Kaushal K. Singh	AMAT/7729/TCG/EPI/RKK 9712	
44257	7590	12/02/2005		EXAMINER	
		ERIDAN, LLP	KUNEMUND, ROBERT M		
3040 POST OAK BOULEVARD, SUITE 1500 HOUSTON, TX 77056			500	ART UNIT	PAPER NUMBER
•				1722	

DATE MAILED: 12/02/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

4	

	Application No.	Applicant(s)					
Office Action Commons	10/688,797	SINGH ET AL.					
Office Action Summary	Examiner	Art Unit					
	Robert M. Kunemund	1722					
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply							
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).							
Status							
1) Responsive to communication(s) filed on	1) Responsive to communication(s) filed on						
2a) ☐ This action is FINAL . 2b) ☑ This) This action is FINAL . 2b) This action is non-final.						
3) Since this application is in condition for allowan	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.							
Disposition of Claims							
4) Claim(s) 67-140 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. 5) Claim(s) is/are allowed. 6) Claim(s) 67-140 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or election requirement.							
Application Papers							
 9) The specification is objected to by the Examiner. 10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner. Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a). Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d). 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152. 							
Priority under 35 U.S.C. § 119							
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 							
. Attachment(s) 1) ☑ Notice of References Cited (PTO-892)	4) 🔲 Interview Summary ((PTO-413)					
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	Paper No(s)/Mail Da						

DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Claims 67, 68, 70 to 76, 80 to 90, 94 to 98, 100 to 110, 112 to 116, 118 to 124, 126 to 128, 130 to 137, 139 and 140 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mizushima et al (6,794,713) in view of Cho et al (6,926,926).

The Mizushima et al reference teaches the deposition of silicon carbides and silicon germanium layers, note entire reference. A substrate is placed in to a vapor deposition chamber. The substrate has masked areas, which create crystalline surfaces and non-crystalline surfaces, note col. 4. The chamber is heated to deposition temperatures, which can be less then 900 c. Then the source gases are fed in to the

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chamber and caused to decompose over the substrate. This deposits the desired layers, note col. 5. The source gases contain silicon, carbon and germanium and are varied to create the desired layers. The deposited layers can have dopant, like phosphorus, note examples. The sole difference between the instant claims and the prior art is the starting silicon gas. However, the Cho et al reference teaches that pentasilanes and derivatives can be used as source gases for silicon in vapor deposition processes, note, col. 3. It would have been obvious to one of ordinary skill in the art to modify the Mizushima et al process by the teachings of the Cho et al reference to use pentasilanes and derivatives in order to lower the impurities and temperatures of deposition increase quality.

Claims 69, 77 to 79, 111, 117, 125 and 129 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mizushima et al (6,794,713) in view of Cho et al (6,926,926).

The Mizushima et al and Cho et al references are relied on for the same reasons as stated, supra, and differ from the instant claims in the temperature and carbon source. However, in the absence of unexpected results, it would have been obvious to one of ordinary skill in the art to determine through routine experimentation the optimum, operable deposition temperatures and carbon source in the Mizushima et al reference in order to increase deposition rates.

Claims 91 to 93 and 138 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mizushima et al (6,794,713) in view of Cho et al (6,926,926).

The Mizushima et al and Cho et al references are relied on for the same reasons as stated, supra, and differ from the instant claims in the etching. However, in the absence of unexpected results, it would have been obvious to one of ordinary skill in the art to determine through routine experimentation the optimum, operable cleaning of the substrate prior to deposition by etching in the Mizushima et al reference in order to increase the quality of the layers by lowering impurities on the substrate surface.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Robert M. Kunemund whose telephone number is 571-272-1464. The examiner can normally be reached on 8 hours.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Duane Smith can be reached on 571-272-1166. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

RMK

ROBERT KUNEMUND/